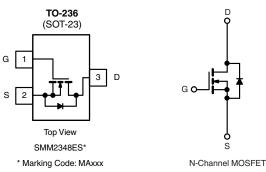


**Vishay Siliconix** 

# Medical N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.024			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.032			
I <sub>D</sub> (A)	8			
Configuration	Single			



### FEATURES

- High Quality Manufacturing Process Using SMM Process Flow
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### APPLICATIONS

Medical

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SMM2348ES-T1-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	30	N	
Gate-Source Voltage		V <sub>GS</sub> ± 20		V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	8		
	T <sub>C</sub> = 125 °C	· I <sub>D</sub>	4.8		
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	2.5	А	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	32		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	15.5		
Single Pulse Avalanche Energy		E <sub>AS</sub>	12	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	PD	3	W	
	T <sub>C</sub> = 125 °C	r_D	1	] **	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	166	°C/W
Junction-to-Foot (Drain)	·		50	0/10

#### Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

b. When mounted on 1" square PCB (FR-4 material).



COMPLIANT

HALOGEN

FREE



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		30	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	v	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V	-	-	1		
	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A	-	0.020	0.024	Ω	
Drain Source On State Resistence?	В	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A, T <sub>J</sub> = 125 °C	-	-	0.036		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 12 A, T <sub>J</sub> = 175 °C	-	-	0.042		
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 8 A	-	0.026	0.032		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 3 A	-	10	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 15 V, f = 1 MHz	-	430	540	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	100	125		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	40	50		
Total Gate Charge <sup>c</sup>	Qg		V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5.5 A	-	7.95	14.5	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V		-	1.6	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	1.3	-		
Gate Resistance	Rg	f = 1 MHz		8.65	17.3	27	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	7	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$V_{DD} = 15 \text{ V}, \text{ R}_{\text{I}} = 3.4 \Omega$		8	15	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 4.4$ A, $V_{GEN} = 10$ V, $R_g = 1 \Omega$		-	21	40		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	15		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	32	А	
Forward Voltage	V <sub>SD</sub>	$I_F = 3.5 \text{ A}, V_{GS} = 0 \text{ V}$		-	0.8	1.2	V	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

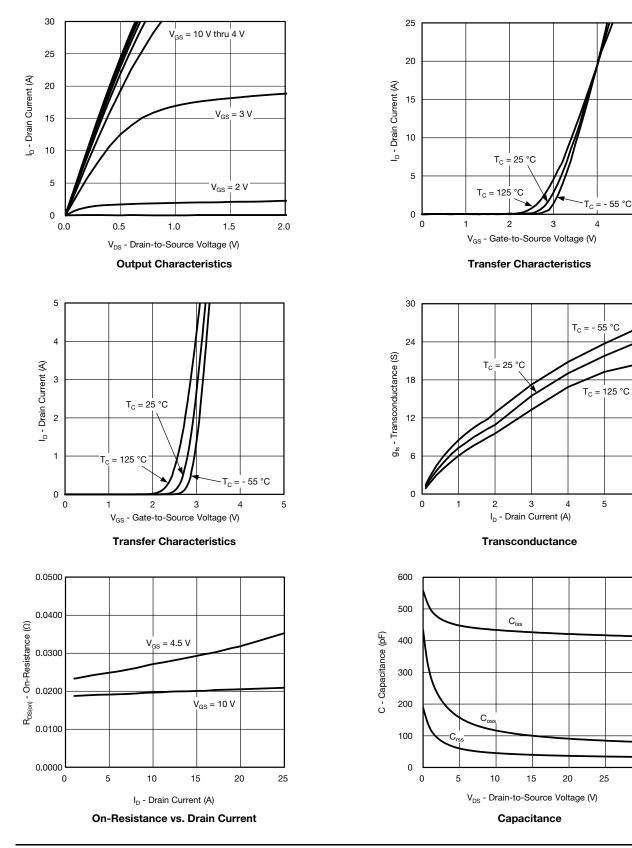


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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



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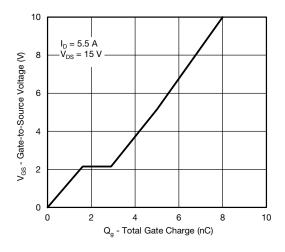
30

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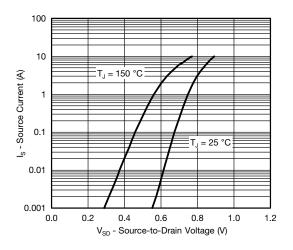


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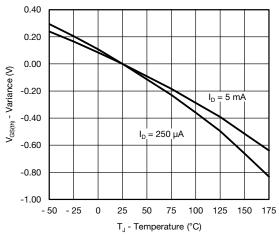
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



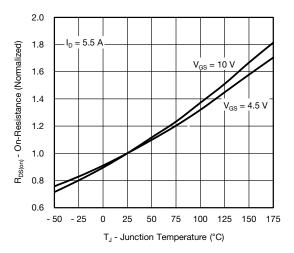
Gate Charge



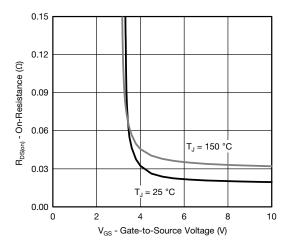
Source Drain Diode Forward Voltage



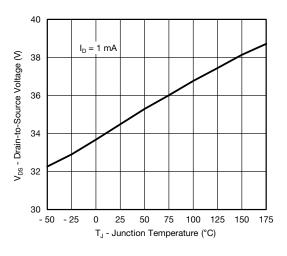
**Threshold Voltage** 



**On-Resistance vs. Junction Temperature** 



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

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4

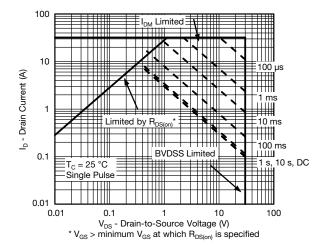
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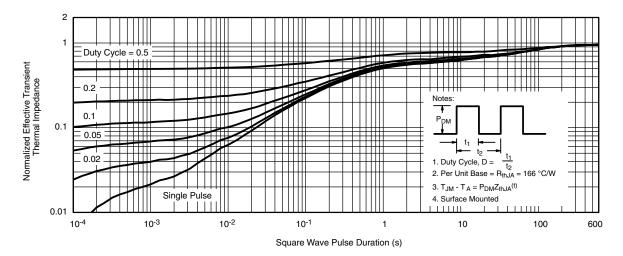


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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Safe Operating Area



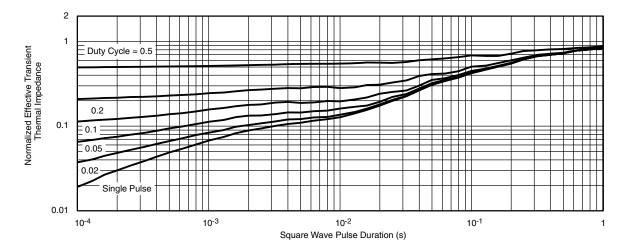
Normalized Thermal Transient Impedance, Junction-to-Ambient

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### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62894.

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